# 2-Input NAND Schmitt-Trigger

The MC74VHC1G132 is a single gate CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G132 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G132 to be used to interface 5V circuits to 3V circuits.

The MC74VHC1G132 can be used to enhance noise immunity or to square up slowly changing waveforms.

- High Speed:  $t_{PD} = 3.6$ ns (Typ) at  $V_{CC} = 5V$
- Low Power Dissipation:  $I_{CC} = 2\mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V

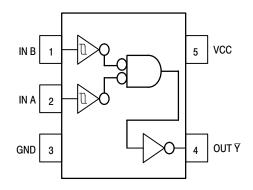


Figure 1. 5-Lead SOT-353 Pinout (Top View)



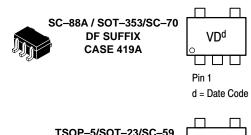
Figure 2. Logic Symbol



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MARKING DIAGRAMS





PIN ASSIGNMENT						
1	IN B					
2	IN A					
3	GND					
4	OUT Y					
5	VCC					

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### **FUNCTION TABLE**

Inp	uts	Output
Α	В	Ϋ́
L	L	Н
L	н	Н
н	L	Н
Н	Н	L

## **MAXIMUM RATINGS\***

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V <sub>CC</sub>	-0.5 to +7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5 to +7.0	V
DC Output Voltage V <sub>CC</sub> = 0 High or Low State	V <sub>OUT</sub>	−0.5 to 7.0 −0.5 to V <sub>CC</sub> + 0.5	V
Input Diode Current	I <sub>IK</sub>	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I <sub>OK</sub>	+20	mA
DC Output Current, per Pin	I <sub>OUT</sub>	+25	mA
DC Supply Current, V <sub>CC</sub> and GND	I <sub>CC</sub>	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

\* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V <sub>CC</sub>	2.0	5.5	V
DC Input Voltage	V <sub>IN</sub>	0.0	5.5	V
DC Output Voltage	V <sub>OUT</sub>	0.0	V <sub>CC</sub>	V
Operating Temperature Range	T <sub>A</sub>	-55	+125	°C

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

#### DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

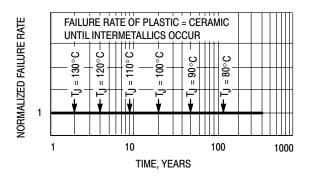


Figure 3. Failure Rate vs. Time Junction Temperature

			V <sub>CC</sub>	ר	Γ <sub>A</sub> = 25°0		<b>T</b> <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ ′	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Мах	Unit
V <sub>T+</sub>	Positive Threshold Voltage		3.0 4.5 5.5	1.50 2.35 2.80	1.88 2.66 3.21	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	V
V <sub>T-</sub>	Negative Threshold Voltage		3.0 4.5 5.5	0.65 1.10 1.45	1.03 1.62 2.02	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	V
V <sub>H</sub>	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
V <sub>OH</sub>	Minimum High–Level Output Voltage I <sub>OH</sub> = –50µA	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I <sub>OH</sub> = -4mA I <sub>OH</sub> = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA

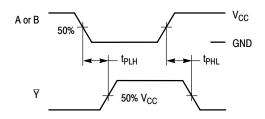
## DC ELECTRICAL CHARACTERISTICS

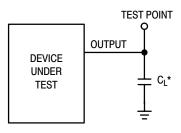
# AC ELECTRICAL CHARACTERISTICS ( $C_{load}$ = 50 pF, Input t<sub>r</sub>/t<sub>f</sub> = 3.0ns)

				T <sub>A</sub> = 25°C			<b>TA</b> ≤	85°C	T <sub>A</sub> ≤ 125°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Мах	Unit
	Maximum Propogation Delay, A	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.6 6.1	11.9 15.4	1.0 1.0	14.0 17.5	1.0 1.0	16.1 19.6	ns
	or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.6 4.3	7.7 9.7	1.0 1.0	9.0 11.0	1.0 1.0	10.3 12.3	
C <sub>IN</sub>	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V		
C <sub>PD</sub>	Power Dissipation Capacitance (Note 1.)	11	pF	Į
4 C in day		ika an anatina a manata an anatina wit	ام مما الدينم ما	

1.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .





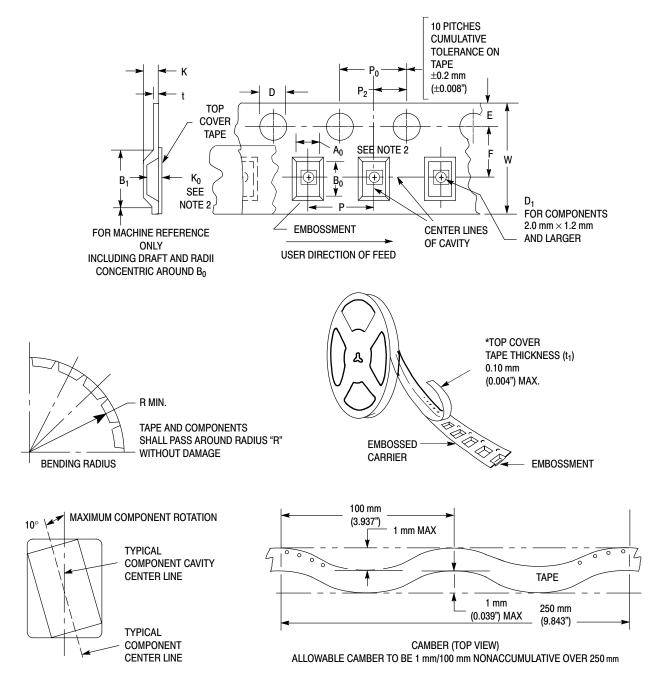
\*Includes all probe and jig capacitance

## Figure 5. Test Circuit

Figure 4. Switching Waveforms

### **DEVICE ORDERING INFORMATION**

			Device Nome	enclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
MC74VHC1G132DFT2	MC	74	VHC1G	132	DF	T2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1G132DFT4	MC	74	VHC1G	132	DF	T4	SC-88A / SOT-353 / SC-70	330 mm (13") 10000 Unit
MC74VHC1G132DTT1	MC	74	VHC1G	132	DT	T1	TSOPS / SOT-23 / SC-59	178 mm (7") 3000 Unit
MC74VHC1G132DTT3	MC	74	VHC1G	132	DT	Т3	TSOPS / SOT-23 / SC-59	330 mm (13") 10000 Unit





Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	E	F	к	Р	Po	P <sub>2</sub>	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

<b>EMBOSSED</b>	CARRIER	DIMENSIONS	(See Note	s 1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO		5 1	

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

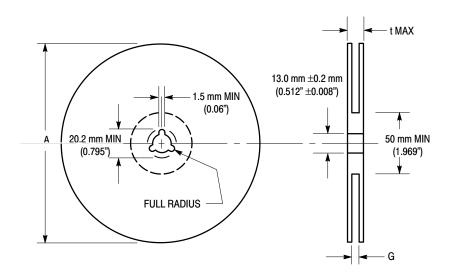


Figure 7. Reel Dimensions

#### **REEL DIMENSIONS**

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")

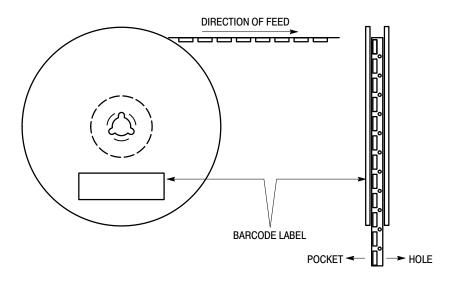
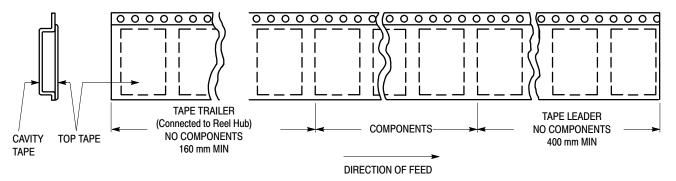
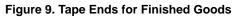
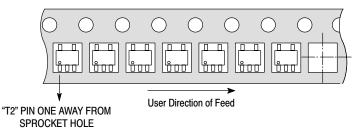
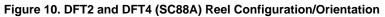


Figure 8. Reel Winding Direction









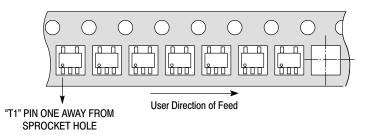
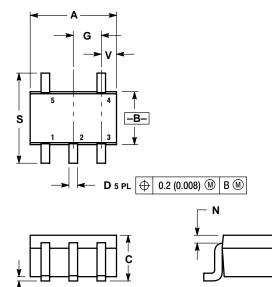


Figure 11. DTT1 and DTT3 (TSOP5) Reel Configuration/Orientation

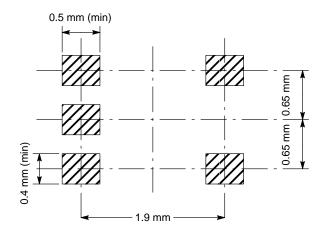
SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B



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NOT	ES:
1.	DIMENSIONING AND TOLERANCING PER ANSI
	Y14.5M, 1982.
2.	CONTROLLING DIMENSION: MM.

	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
Н		0.004		0.10
ſ	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
٧	0.012	0.016	0.30	0.40



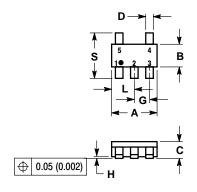
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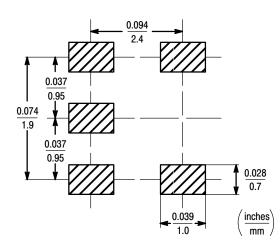
TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 **ISSUE A** 

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NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J K	0.10	0.26	0.0040	0.0102
	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181





# <u>Notes</u>

# <u>Notes</u>

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